



20V N-Channel Enhancement Mode MOSFET

Voltage 20 V Current 4.1A

Features

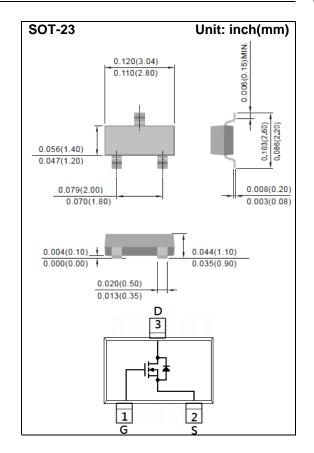
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@4.1A<56m\Omega$
- $R_{DS(ON)}$, $V_{GS}@2.5V$, $I_{D}@2.8A<68m\Omega$
- R_{DS(ON)} , V_{GS}@1.8V, I_D@1.5A<95mΩ
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC61249 standard

Mechanical Data

• Case: SOT-23 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0003 ounces, 0.0084 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAME	SYMBOL	LIMIT	UNITS		
Drain-Source Voltage	V _{DS}	20	V		
Gate-Source Voltage	V_{GS}	<u>+</u> 12			
Continuous Drain Current		I _D	4.1	A	
Pulsed Drain Current		I _{DM}	16.4		
B	T _a =25°C	P_D	1.25	W	
Power Dissipation	Derate above 25°C		10	mW/°C	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance					
- Junction to Ambient (Note 3)		$R_{\theta JA}$	100	°C/W	





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} =0V, I _D =250uA	20	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	0.4	0.66	1.2			
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =4.1A	-	41	56	mΩ		
		V _{GS} =2.5V, I _D =2.8A	-	50	68			
		V _{GS} =1.8V, I _D =1.5A	-	66	95			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V	-	-	1	uA		
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 12V, V _{DS} =0V	-	-	<u>+</u> 100	nA		
Dynamic (Note 5)								
Total Gate Charge	Q_g	\/ 40\/ I 44A	-	4.6	-	nC		
Gate-Source Charge	Q_gs	V_{DS} =10V, I_{D} =4.1A, V_{GS} =4.5V (Note 1,2)	-	0.8	-			
Gate-Drain Charge	Q_gd		-	1	-			
Input Capacitance	Ciss	V _{DS} =10V, V _{GS} =0V, f=1MHZ	-	350	-	pF		
Output Capacitance	Coss		-	40	-			
Reverse Transfer Capacitance	Crss		-	29	-			
Turn-On Delay Time	td _(on)	V_{DD} =10V, I_{D} =4.1A, V_{GS} =4.5V, R_{G} =6 Ω (Note 1,2)	-	4	-			
Turn-On Rise Time	tr		-	47	-	ns		
Turn-Off Delay Time	td _(off)		-	18	-			
Turn-Off Fall Time	tf		-	10	-			
Drain-Source Diode								
Maximum Continuous Drain-Source	ı				1.5	А		
Diode Forward Current	I _S		_	-	1.5			
Diode Forward Voltage	V_{SD}	I _S =1A, V _{GS} =0V	-	0.75	1.2	V		

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

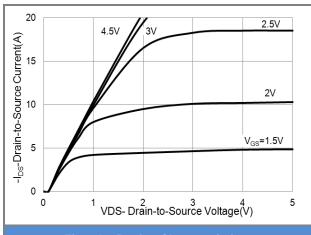


Fig.1 On-Region Characteristics

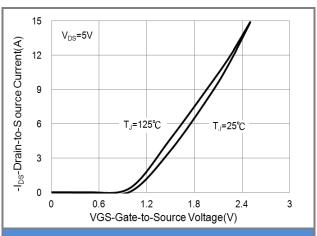


Fig.2 Transfer Characteristics

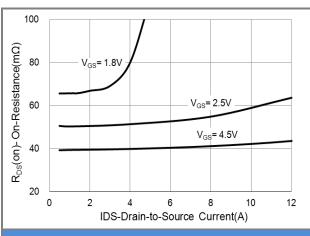


Fig.3 On-Resistance vs. Drain Current

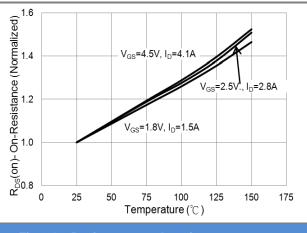
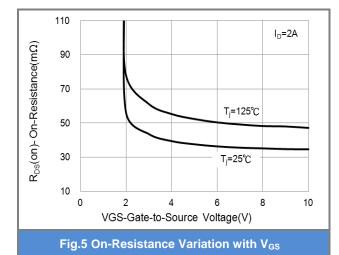
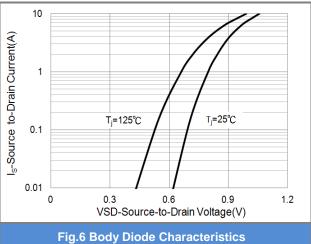


Fig.4 On-Resistance vs. Junction temperature









TYPICAL CHARACTERISTIC CURVES

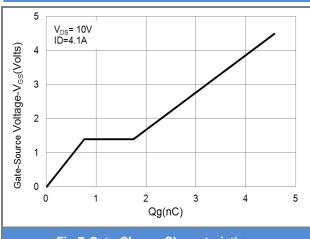


Fig.7 Gate-Charge Characteristics

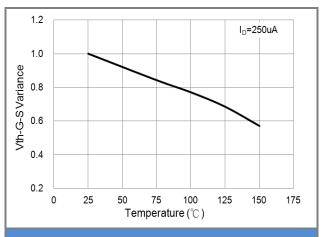


Fig.8 Threshold Voltage Variation with Temperature

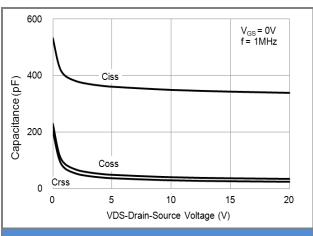


Fig.9 Capacitance vs. Drain-Source Voltage

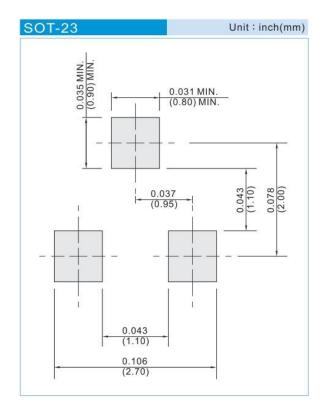




Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJA3412_R1_00001	SOT-23	3K pcs / 7" reel	A12	Halogen free

Mounting Pad Layout







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